

Jihyun Kim

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

224
papers

6,506
citations

41
h-index

73
g-index

232
ext. papers

7,769
ext. citations

3.9
avg, IF

6.38
L-index

#	Paper	IF	Citations
224	Growth and Fabrication of GaAs Thin-Film Solar Cells on a Si Substrate via Hetero Epitaxial Lift-Off. <i>Applied Sciences (Switzerland)</i> , 2022 , 12, 820	2.6	1
223	Capacitance-voltage characteristics of Pt/hBN/WSe ₂ metal-insulator-semiconductor capacitor doped by charge-transfer process. <i>Applied Physics Letters</i> , 2022 , 120, 023102	3.4	
222	Deep level defect states in α -Ga ₂ O ₃ and e-Ga ₂ O ₃ crystals and films: Impact on device performance. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2022 , 40, 020804	2.9	11
221	Exfoliated and bulk α -gallium oxide electronic and photonic devices 2022 , 1, 100001		0
220	H trapping at the metastable cation vacancy in α -Ga ₂ O ₃ and α -Al ₂ O ₃ . <i>Applied Physics Letters</i> , 2022 , 120, 192101	3.4	2
219	1 GeV proton damage in α -Ga ₂ O ₃ . <i>Journal of Applied Physics</i> , 2021 , 130, 185701	2.5	1
218	Improving the oxygen evolution reaction using electronic structure modulation of sulfur-retaining nickel-based electrocatalysts. <i>Journal of Materials Chemistry A</i> , 2021 , 9, 27034-27040	13	1
217	Self-powered solar-blind α -Ga ₂ O ₃ thin-film UV-C photodiode grown by halide vapor-phase epitaxy. <i>APL Materials</i> , 2021 , 9, 101108	5.7	2
216	Selective p-Doping of 2D WSe ₂ UV/Ozone Treatments and Its Application in Field-Effect Transistors. <i>ACS Applied Materials & Interfaces</i> , 2021 , 13, 955-961	9.5	9
215	Achieving over 15% Efficiency in Solution-Processed Cu(In,Ga)(S,Se) Thin-Film Solar Cells via a Heterogeneous-Formation-Induced Benign p-n Junction Interface. <i>ACS Applied Materials & Interfaces</i> , 2021 , 13, 13289-13300	9.5	4
214	Artificial Neuron and Synapse Devices Based on 2D Materials. <i>Small</i> , 2021 , 17, e2100640	11	17
213	Large-scale synthesis of atomically thin ultrawide bandgap α -Ga ₂ O ₃ using a liquid gallium squeezing technique. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2021 , 39, 033409	2.9	4
212	Review Radiation Damage in Wide and Ultra-Wide Bandgap Semiconductors. <i>ECS Journal of Solid State Science and Technology</i> , 2021 , 10, 055008	2	19
211	Neuromorphic Devices: Artificial Neuron and Synapse Devices Based on 2D Materials (Small 20/2021). <i>Small</i> , 2021 , 17, 2170092	11	
210	High responsivity solar-blind metal-semiconductor-metal photodetector based on α -Ga ₂ O ₃ . <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2021 , 39, 033410	2.9	9
209	Reactivity of sulfur compounds in FCC decant oils for hydrodesulfurization over CoMoS ₂ /Al ₂ O ₃ catalysts. <i>Korean Journal of Chemical Engineering</i> , 2021 , 38, 1179-1187	2.8	1
208	Electrical properties and deep trap spectra in Ga ₂ O ₃ films grown by halide vapor phase epitaxy on p-type diamond substrates. <i>Journal of Applied Physics</i> , 2021 , 129, 185701	2.5	6

207	Defect-Engineered n-Doping of WSe ₂ via Argon Plasma Treatment and Its Application in Field-Effect Transistors. <i>Advanced Materials Interfaces</i> , 2021 , 8, 2100718	4.6	4
206	Photoelectrochemical etching of ultra-wide bandgap β -Ga ₂ O ₃ semiconductor in phosphoric acid and its optoelectronic device application. <i>Applied Surface Science</i> , 2021 , 539, 148130	6.7	7
205	Design of Ga ₂ O ₃ modulation doped field effect transistors. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2021 , 39, 023412	2.9	4
204	Magneto-optical properties of Cr ³⁺ in β -Ga ₂ O ₃ . <i>Applied Physics Letters</i> , 2021 , 119, 052101	3.4	8
203	Capacitive β -Ga ₂ O ₃ solar-blind photodetector with graphene electrode. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2021 , 39, 053412	2.9	1
202	Assessment of the (010) β -Ga ₂ O ₃ surface and substrate specification. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2021 , 39, 013408	2.9	2
201	(100) Plane β -Ga ₂ O ₃ Flake Based Field Effect Transistor and Its Hydrogen Response. <i>ECS Journal of Solid State Science and Technology</i> , 2021 , 10, 125004	2	0
200	Morphological-Electrical Property Relation in Cu(In,Ga)(S,Se) Solar Cells: Significance of Crystal Grain Growth and Band Grading by Potassium Treatment. <i>Small</i> , 2020 , 16, e2003865	11	7
199	An in-plane WSe ₂ p β homojunction two-dimensional diode by laser-induced doping. <i>Journal of Materials Chemistry C</i> , 2020 , 8, 8393-8398	7.1	8
198	Alpha Particle Irradiation of High Aluminum Content AlGa _n Polarization Doped Field Effect Transistors. <i>ECS Journal of Solid State Science and Technology</i> , 2020 , 9, 035008	2	2
197	Ambipolar Charge Transport in Two-Dimensional WS ₂ Metal-Insulator-Semiconductor and Metal-Insulator-Semiconductor Field-Effect Transistors. <i>ACS Applied Materials & Interfaces</i> , 2020 , 12, 23127-23133	9.5	9
196	Programmable Synapse-Like MoS ₂ Field-Effect Transistors Phase-Engineered by Dynamic Lithium Ion Modulation. <i>Advanced Electronic Materials</i> , 2020 , 6, 1901410	6.4	9
195	BCl ₃ -Based Dry Etching of Exfoliated (100) β -Ga ₂ O ₃ Flakes. <i>ECS Journal of Solid State Science and Technology</i> , 2020 , 9, 075001	2	3
194	Capacitive Chemical Sensors Based on Two-Dimensional WSe ₂ . <i>ECS Journal of Solid State Science and Technology</i> , 2020 , 9, 115020	2	4
193	Preface IASS Focus Issue on Gallium Oxide Based Materials and Devices II. <i>ECS Journal of Solid State Science and Technology</i> , 2020 , 9, 060001	2	0
192	Highly selective ozone-treated β -Ga ₂ O ₃ solar-blind deep-UV photodetectors. <i>Applied Physics Letters</i> , 2020 , 117, 261101	3.4	15
191	Dual-field plated β -Ga ₂ O ₃ nano-FETs with an off-state breakdown voltage exceeding 400 V. <i>Journal of Materials Chemistry C</i> , 2020 , 8, 2687-2692	7.1	5
190	Monolithically Integrated Enhancement-Mode and Depletion-Mode β -GaO MESFETs with Graphene-Gate Architectures and Their Logic Applications. <i>ACS Applied Materials & Interfaces</i> , 2020 , 12, 7310-7316	9.5	19

189	Ultra-Wide Bandgap EGa_2O_3 Heterojunction Field-Effect Transistor Using p-Type 4H-SiC Gate for Efficient Thermal Management. <i>ECS Journal of Solid State Science and Technology</i> , 2020 , 9, 065006	2	3
188	Ultrawide-Bandgap p-n Heterojunction of Diamond/ EGa_2O_3 for a Solar-Blind Photodiode. <i>ECS Journal of Solid State Science and Technology</i> , 2020 , 9, 045004	2	20
187	Radiation damage effects in Ga_2O_3 materials and devices. <i>Journal of Materials Chemistry C</i> , 2019 , 7, 10-241	4.1	90
186	Nafion membranes with a sulfonated organic additive for the use in vanadium redox flow batteries. <i>Journal of Applied Polymer Science</i> , 2019 , 136, 47547	2.9	14
185	Controlling the threshold voltage of EGa_2O_3 field-effect transistors via remote fluorine plasma treatment. <i>Journal of Materials Chemistry C</i> , 2019 , 7, 8855-8860	7.1	13
184	Will surface effects dominate in quasi-two-dimensional gallium oxide for electronic and photonic devices?. <i>Nanoscale Horizons</i> , 2019 , 4, 1251-1255	10.8	8
183	Auto-Masked Surface Texturing of Kerf-Loss Free Silicon Wafers Using Hexafluoroisopropanol in a Capacitively Coupled Plasma Etching System. <i>ECS Journal of Solid State Science and Technology</i> , 2019 , 8, Q76-Q79	2	3
182	Electrical Properties of Thermally Annealed EGa_2O_3 Metal-Semiconductor Field-Effect Transistors with Pt/Au Schottky Contacts. <i>ECS Journal of Solid State Science and Technology</i> , 2019 , 8, Q3122-Q3125	2	3
181	Photo-Enhanced Acid Chemical Etching of High-Quality Aluminum Nitride Grown by Metal-Organic Chemical Vapor Deposition. <i>ECS Journal of Solid State Science and Technology</i> , 2019 , 8, N42-N46	2	5
180	Ultrahigh Deep-UV Sensitivity in Graphene-Gated EGa_2O_3 Phototransistors. <i>ACS Photonics</i> , 2019 , 6, 1026-1032	6.3	48
179	Heterojunction Bipolar Transistor: 2D Material-Based Vertical Double Heterojunction Bipolar Transistors with High Current Amplification (Adv. Electron. Mater. 3/2019). <i>Advanced Electronic Materials</i> , 2019 , 5, 1970015	6.4	1
178	Field-plate engineering for high breakdown voltage EGaO nanolayer field-effect transistors.. <i>RSC Advances</i> , 2019 , 9, 9678-9683	3.7	17
177	^{60}Co Gamma Ray Damage in Homoepitaxial EGa_2O_3 Schottky Rectifiers. <i>ECS Journal of Solid State Science and Technology</i> , 2019 , 8, Q3041-Q3045	2	10
176	Intimate Ohmic contact to two-dimensional WSe via thermal alloying. <i>Nanotechnology</i> , 2019 , 30, 415302	3.4	1
175	All-2D ReS transistors with split gates for logic circuitry. <i>Scientific Reports</i> , 2019 , 9, 10354	4.9	13
174	Programmable Multilevel Memtransistors Based on van der Waals Heterostructures. <i>Advanced Electronic Materials</i> , 2019 , 5, 1900333	6.4	15
173	High-energy proton irradiation damage on two-dimensional hexagonal boron nitride.. <i>RSC Advances</i> , 2019 , 9, 18326-18332	3.7	
172	Annealing of Proton and Alpha Particle Damage in Au-W/ EGa_2O_3 Rectifiers. <i>ECS Journal of Solid State Science and Technology</i> , 2019 , 8, P799-P804	2	1

171	2D Material-Based Vertical Double Heterojunction Bipolar Transistors with High Current Amplification. <i>Advanced Electronic Materials</i> , 2019 , 5, 1800745	6.4	16
170	Defect States Determining Dynamic Trapping-Detrapping in EGa_2O_3 Field-Effect Transistors. <i>ECS Journal of Solid State Science and Technology</i> , 2019 , 8, Q3013-Q3018	2	19
169	Radiation damage in Ga_2O_3 2019 , 313-328		4
168	Ga_2O_3 nanobelt devices 2019 , 331-368		1
167	Two-Dimensionally Layered p-Black Phosphorus/n-MoS/p-Black Phosphorus Heterojunctions. <i>ACS Applied Materials & Interfaces</i> , 2018 , 10, 10347-10352	9.5	32
166	Chemical Doping Effects of Gas Molecules on Black Phosphorus Field-Effect Transistors. <i>ECS Journal of Solid State Science and Technology</i> , 2018 , 7, Q3065-Q3069	2	8
165	Point defect induced degradation of electrical properties of Ga_2O_3 by 10 MeV proton damage. <i>Applied Physics Letters</i> , 2018 , 112, 032107	3.4	72
164	Deep-ultraviolet photodetector based on exfoliated n-type EGa_2O_3 nanobelt/p-Si substrate heterojunction. <i>Korean Journal of Chemical Engineering</i> , 2018 , 35, 574-578	2.8	23
163	High Responsivity EGa_2O_3 Metal Semiconductor Metal Solar-Blind Photodetectors with Ultraviolet Transparent Graphene Electrodes. <i>ACS Photonics</i> , 2018 , 5, 1123-1128	6.3	147
162	Reducing the contact and channel resistances of black phosphorus via low-temperature vacuum annealing. <i>Journal of Materials Chemistry C</i> , 2018 , 6, 1567-1572	7.1	15
161	A review of Ga_2O_3 materials, processing, and devices. <i>Applied Physics Reviews</i> , 2018 , 5, 011301	17.3	1114
160	10 MeV proton damage in EGa_2O_3 Schottky rectifiers. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2018 , 36, 011206	1.3	24
159	High breakdown voltage quasi-two-dimensional EGa_2O_3 field-effect transistors with a boron nitride field plate. <i>Applied Physics Letters</i> , 2018 , 112, 122102	3.4	63
158	A 0.02mm ² fully synthesizable period-jitter sensor using stochastic TDC without reference clock and calibration in 10nm CMOS technology 2018 ,		4
157	Enhancing ambipolar carrier transport of black phosphorus field-effect transistors with Ni-P alloy contacts. <i>Physical Chemistry Chemical Physics</i> , 2018 , 20, 22439-22444	3.6	3
156	Tuning the Threshold Voltage of Exfoliated EGa_2O_3 Flake-Based Field-Effect Transistors by Photo-Enhanced H_3PO_4 Wet Etching. <i>ECS Journal of Solid State Science and Technology</i> , 2018 , 7, Q148-Q151	1	15
155	Bifacial CdS/CdTe thin-film solar cells using a transparent silver nanowire/indium tin oxide back contact. <i>Optics Express</i> , 2018 , 26, A30-A38	3.3	16
154	Diffusion length of non-equilibrium minority charge carriers in EGa_2O_3 measured by electron beam induced current. <i>Journal of Applied Physics</i> , 2018 , 123, 185704	2.5	37

153	Eighteen mega-electron-volt alpha-particle damage in homoepitaxial EGa_2O_3 Schottky rectifiers. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2018 , 36, 031205	1.3	13
152	High performance black phosphorus field-effect transistors with vacuum-annealed low-resistance Ohmic contact 2018 ,		1
151	Heterostructure WSe-GaO Junction Field-Effect Transistor for Low-Dimensional High-Power Electronics. <i>ACS Applied Materials & Interfaces</i> , 2018 , 10, 29724-29729	9.5	60
150	Rapid and Accurate Measurement of Ideality Factor and Parasitic Resistances of Thin Film Solar Cells. <i>ECS Journal of Solid State Science and Technology</i> , 2018 , 7, Q105-Q108	2	1
149	Radiation and process-induced damage in Ga_2O_3 2018 ,		1
148	Perspective: Ga_2O_3 for ultra-high power rectifiers and MOSFETS. <i>Journal of Applied Physics</i> , 2018 , 124, 220901	2.5	245
147	High Gain EGa_2O_3 Solar-Blind Schottky Barrier Photodiodes via Carrier Multiplication Process. <i>ECS Journal of Solid State Science and Technology</i> , 2018 , 7, Q196-Q200	2	7
146	Effect of proton irradiation energy on $\text{SiN}_x/\text{AlGaIn}/\text{GaIn}$ metal-insulator semiconductor high electron mobility transistors. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2018 , 36, 052202	1.3	11
145	Defects responsible for charge carrier removal and correlation with deep level introduction in irradiated EGa_2O_3 . <i>Applied Physics Letters</i> , 2018 , 113, 092102	3.4	46
144	Reducing the Optical Reflectance of Kerf-Loss Free Silicon Wafers via Auto-Masked CF_4/O_2 Plasma Etch. <i>ECS Journal of Solid State Science and Technology</i> , 2018 , 7, Q88-Q91	2	2
143	Hydrogen Sensing Characteristics of Pt Schottky Diodes on () and (010) Ga_2O_3 Single Crystals. <i>ECS Journal of Solid State Science and Technology</i> , 2018 , 7, Q3180-Q3182	2	15
142	High reverse breakdown voltage Schottky rectifiers without edge termination on Ga_2O_3 . <i>Applied Physics Letters</i> , 2017 , 110, 192101	3.4	118
141	1.5 MeV electron irradiation damage in EGa_2O_3 vertical rectifiers. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2017 , 35, 031208	1.3	41
140	Perspective Opportunities and Future Directions for Ga_2O_3 . <i>ECS Journal of Solid State Science and Technology</i> , 2017 , 6, P356-P359	2	261
139	Suspended black phosphorus nanosheet gas sensors. <i>Sensors and Actuators B: Chemical</i> , 2017 , 250, 569-573	3.3	80
138	Platinum-functionalized black phosphorus hydrogen sensors. <i>Applied Physics Letters</i> , 2017 , 110, 242103	3.4	38
137	Quasi-Two-Dimensional h-BN/ EGaO Heterostructure Metal-Insulator-Semiconductor Field-Effect Transistor. <i>ACS Applied Materials & Interfaces</i> , 2017 , 9, 21322-21327	9.5	71
136	Recovery of the Pristine Surface of Black Phosphorus by Water Rinsing and Its Device Application. <i>ACS Applied Materials & Interfaces</i> , 2017 , 9, 21382-21389	9.5	9

135	Tuning the thickness of exfoliated quasi-two-dimensional EGa_2O_3 flakes by plasma etching. <i>Applied Physics Letters</i> , 2017 , 110, 131901	3.4	54
134	Electrospun Nb-doped TiO nanofiber support for Pt nanoparticles with high electrocatalytic activity and durability. <i>Scientific Reports</i> , 2017 , 7, 44411	4.9	45
133	Influence of High-Energy Proton Irradiation on EGaO Nanobelt Field-Effect Transistors. <i>ACS Applied Materials & Interfaces</i> , 2017 , 9, 40471-40476	9.5	76
132	Solar-Blind Metal-Semiconductor-Metal Photodetectors Based on an Exfoliated EGa_2O_3 Micro-Flake. <i>ECS Journal of Solid State Science and Technology</i> , 2017 , 6, Q79-Q83	2	65
131	Contacting Mechanically Exfoliated EGa_2O_3 Nanobelts for (Opto)electronic Device Applications. <i>ECS Journal of Solid State Science and Technology</i> , 2017 , 6, Q3045-Q3048	2	19
130	Optical Signature of the Electron Injection in Ga_2O_3 . <i>ECS Journal of Solid State Science and Technology</i> , 2017 , 6, Q3049-Q3051	2	9
129	Electrical Characteristics of Vertical Ni/ EGa_2O_3 Schottky Barrier Diodes at High Temperatures. <i>ECS Journal of Solid State Science and Technology</i> , 2017 , 6, Q3022-Q3025	2	73
128	Chemical etching behavior of non-polar GaN sidewalls. <i>Journal of Crystal Growth</i> , 2016 , 456, 108-112	1.6	2
127	Tuning the thickness of black phosphorus via ion bombardment-free plasma etching for device performance improvement. <i>Journal of Materials Chemistry C</i> , 2016 , 4, 6234-6239	7.1	34
126	In situ thickness control of black phosphorus field-effect transistors via ozone treatment. <i>Nano Research</i> , 2016 , 9, 3056-3065	10	17
125	Quasi-two-dimensional Gallium oxide solar-blind photodetectors with ultrahigh responsivity. <i>Journal of Materials Chemistry C</i> , 2016 , 4, 9245-9250	7.1	89
124	Transfer-Free Growth of Multilayer Graphene Using Self-Assembled Monolayers. <i>ACS Applied Materials & Interfaces</i> , 2016 , 8, 27115-27121	9.5	20
123	Graphene-based Chemical Sensors 2016 , 221-243		
122	Body-Attachable and Stretchable Multisensors Integrated with Wirelessly Rechargeable Energy Storage Devices. <i>Advanced Materials</i> , 2016 , 28, 748-56	24	102
121	A Comparative Study of Nanoparticle-Ink-Based CIGSSe Thin Film Solar Cells on Different Back Contact Substrates. <i>Bulletin of the Korean Chemical Society</i> , 2016 , 37, 361-365	1.2	1
120	Defect-engineered graphene chemical sensors with ultrahigh sensitivity. <i>Physical Chemistry Chemical Physics</i> , 2016 , 18, 14198-204	3.6	82
119	Electrical and Optical Damage to GaN-Based Light-Emitting Diodes by 20-MeV Proton Irradiation. <i>Science of Advanced Materials</i> , 2016 , 8, 160-163	2.3	7
118	Elevated temperature performance of Si-implanted solar-blind EGa_2O_3 photodetectors. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2016 , 34, 041207	1.3	20

117	Effect of 5 MeV proton irradiation damage on performance of Ga_2O_3 photodetectors. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2016 , 34, 041213	1.3	47
116	Effect of front and back gates on Ga_2O_3 nano-belt field-effect transistors. <i>Applied Physics Letters</i> , 2016 , 109, 062102	3.4	79
115	Effects of proton irradiation and thermal annealing on off-state step-stressed AlGaN/GaN high electron mobility transistors. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2016 , 34, 041231	1.3	6
114	Exfoliated Ga_2O_3 nano-belt field-effect transistors for air-stable high power and high temperature electronics. <i>Physical Chemistry Chemical Physics</i> , 2016 , 18, 15760-4	3.6	111
113	Radiation-Hard and Ultralightweight Polycrystalline Cadmium Telluride Thin-Film Solar Cells for Space Applications. <i>Energy Technology</i> , 2016 , 4, 1463-1468	3.5	2
112	Probing patterned defects on graphene using differential interference contrast observation. <i>Applied Physics Letters</i> , 2015 , 106, 081901	3.4	5
111	Lattice distortion analysis of nonpolar a-plane ((11 $\bar{2}$ 0)) GaN films by using a grazing-incidence X-ray diffraction technique. <i>Journal of the Korean Physical Society</i> , 2015 , 66, 607-611	0.6	2
110	15.5 A 0.6V 1.17ps PVT-tolerant and synthesizable time-to-digital converter using stochastic phase interpolation with 16 \times spatial redundancy in 14nm FinFET technology 2015 ,		15
109	Fabrication of a stretchable and patchable array of high performance micro-supercapacitors using a non-aqueous solvent based gel electrolyte. <i>Energy and Environmental Science</i> , 2015 , 8, 1764-1774	35.4	115
108	Precise control of defects in graphene using oxygen plasma. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2015 , 33, 060602	2.9	28
107	Chalcogenization-Derived Band Gap Grading in Solution-Processed $\text{CuIn}_x\text{Ga}_{1-x}(\text{Se,S})$ Thin-Film Solar Cells. <i>ACS Applied Materials & Interfaces</i> , 2015 , 7, 27391-6	9.5	30
106	Effect of proton irradiation energy on AlGaN/GaN metal-oxide semiconductor high electron mobility transistors. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2015 , 33, 051208	1.3	8
105	Effects of 340 keV proton irradiation on InGaN/GaN blue light-emitting diodes. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2015 , 33, 051215	1.3	11
104	Effects of defect density on ultrathin graphene-based metal diffusion barriers. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2015 , 33, 061510	2.9	5
103	Development of solar-blind photodetectors based on Si-implanted Ga_2O_3 . <i>Optics Express</i> , 2015 , 23, 28300-5	3.3	76
102	Energy and dose dependence of proton-irradiation damage in graphene. <i>RSC Advances</i> , 2015 , 5, 31861-31865	3.865	17
101	A simple chemical route for composition graded $\text{Cu}(\text{In,Ga})\text{S}_2$ thin film solar cells: multi-stage paste coating. <i>RSC Advances</i> , 2015 , 5, 103439-103444	3.7	6
100	Layer-by-layer AuCl_3 doping of stacked graphene films. <i>Physica Status Solidi - Rapid Research Letters</i> , 2014 , 8, 441-444	2.5	10

99	Chemical bath deposition of cadmium sulfide on graphene-coated flexible glass substrate. <i>Applied Physics Letters</i> , 2014 , 104, 133902	3.4	7
98	Radiation Damage in GaN-Based Materials and Devices 2014 , 345-387		3
97	III-nitride nanowire based light emitting diodes on carbon paper. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2014 , 11, 442-445		1
96	Selective deposition of graphene sheets on a flexible substrate by a nonuniform electric field. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2014 , 32, 020602	1.3	3
95	Chemical etching behaviors of semipolar (11 22) and nonpolar (11 20) gallium nitride films. <i>Physical Chemistry Chemical Physics</i> , 2014 , 16, 15780-3	3.6	17
94	Study on the effects of proton irradiation on the dc characteristics of AlGaIn/GaN high electron mobility transistors with source field plate. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2014 , 32, 022202	1.3	12
93	Rapid sintering of TiO ₂ photoelectrodes using intense pulsed white light for flexible dye-sensitized solar cells. <i>Applied Physics Letters</i> , 2014 , 104, 143902	3.4	21
92	GaN-based light-emitting diodes on graphene-coated flexible substrates. <i>Optics Express</i> , 2014 , 22 Suppl 3, A812-7	3.3	12
91	Review of radiation damage in GaN-based materials and devices. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2013 , 31, 050801	2.9	145
90	Nonpolar light emitting diode with sharp near-ultraviolet emissions using hydrothermally grown ZnO on p-GaN. <i>Applied Physics Letters</i> , 2013 , 103, 091107	3.4	23
89	A study on information transfer rate by brain-computer interface (BCI) using functional near-infrared spectroscopy (fNIRS) 2013 ,		1
88	Three-Dimensional Graphene Network-Based Chemical Sensors on Paper Substrate. <i>Journal of the Electrochemical Society</i> , 2013 , 160, B160-B163	3.9	22
87	Radiation effects in GaN materials and devices. <i>Journal of Materials Chemistry C</i> , 2013 , 1, 877-887	7.1	139
86	Three-dimensional graphene foam-based transparent conductive electrodes in GaN-based blue light-emitting diodes. <i>Applied Physics Letters</i> , 2013 , 102, 161902	3.4	32
85	Flexible graphene-based chemical sensors on paper substrates. <i>Physical Chemistry Chemical Physics</i> , 2013 , 15, 1798-801	3.6	109
84	A facile method for highly uniform GaN-based nanorod light-emitting diodes with InGaIn/GaN multi-quantum-wells. <i>Optics Express</i> , 2013 , 21, 12908-13	3.3	8
83	GaN-based ultraviolet light-emitting diodes with AuCl ₃ -doped graphene electrodes. <i>Optics Express</i> , 2013 , 21, 29025-30	3.3	34
82	Impact of proton irradiation on dc performance of AlGaIn/GaN high electron mobility transistors. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2013 , 31, 042202	1.3	20

81	Nickel Foam as a Substrate for III-nitride Nanowire Growth. <i>Materials Research Society Symposia Proceedings</i> , 2013 , 1538, 311-316		
80	Growth of CdTe thin films on graphene by close-spaced sublimation method. <i>Applied Physics Letters</i> , 2013 , 103, 231910	3.4	18
79	CdTe microwire-based ultraviolet photodetectors aligned by a non-uniform electric field. <i>Applied Physics Letters</i> , 2013 , 103, 051906	3.4	13
78	Dependence on proton energy of degradation of AlGaIn/GaN high electron mobility transistors. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2013 , 31, 022201	1.3	29
77	Electrical characterization of ⁶⁰ Co gamma radiation-exposed InAlN/GaN high electron mobility transistors. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2013 , 31, 051210	1.3	10
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